## Modification of SiO<sub>2</sub> powders by using a MDFR

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Recently, various kinds of attempts have been made to avoid the formation of undesirable components during the formation of main target materials. One of them is the incorporation of target materials to inert media such as SiO<sub>2</sub>. However, the SiO<sub>2</sub> should be modified to be applied in a specific target usage and field. To explore the new functions and characteristics of SiO<sub>2</sub> powders,  $Zn^{2+}$  were doped into the surface of SiO<sub>2</sub> powders. A MDFR was employed to prepare SiO<sub>2</sub>:Zn powders continuously and effectively. Effects of continuous U<sub>C</sub>, U<sub>MB</sub> and C<sub>Zn</sub> on the structural, optical and electrical properties of SiO<sub>2</sub>:Zn powders were investigated. Some parts of Si<sup>4+</sup> in the host materials were substituted by Zn<sup>2+</sup>. The substitution was promoted by increasing in U<sub>MB</sub>. The substitution of Si<sup>4+</sup> by Zn<sup>2+</sup> could reduce the bandgap energy between the conduction band of Si<sup>4+</sup> and the valence band of O<sub>2p</sub>. The increase in U<sub>MB</sub> led to the reduction of bandgap energy of SiO<sub>2</sub>:Zn powders by forming an intrinsic energy level such as acceptor level to the conduction band. SEM analysis showed that the SiO<sub>2</sub>:Zn powders were spherical and highly porous with extremely wrinkled and furrowed, with increasing U<sub>MB</sub> and C<sub>Zn</sub>.